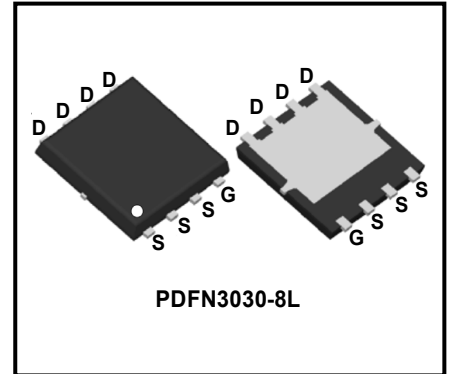


65V N-Channel Enhancement Mode Power MOSFET

Description

WMQ048NV6HG4 uses Wayon's 4th generation power trench MOSFET technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance. This device is well suited for high efficiency fast switching applications.



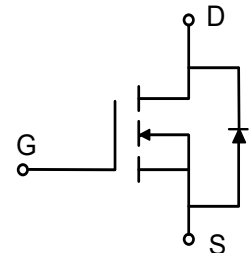
Features

- $V_{DS} = 65V$, $I_D = 68A$
 $R_{DS(on)} < 5.5m\Omega @ V_{GS} = 10V$
- Low $R_{DS(on)}$
- 100% EAS Guaranteed
- High Speed Power Switching



Applications

- Synchronous Rectification
- DC/DC Converter



Absolute Maximum Ratings ($T_A = 25^\circ C$, unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|----------------|---------------------|------------|
| Drain-Source Voltage | V_{DS} | 65 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | $T_C = 25^\circ C$ | 68 |
| | | $T_C = 100^\circ C$ | 43 |
| Pulsed Drain Current ¹ | I_{DM} | 272 | A |
| Single Pulse Avalanche Energy ² | EAS | 135.2 | mJ |
| Total Power Dissipation | P_D | 43 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ C$ |

Thermal Characteristics

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------|--------------|
| Thermal Resistance from Junction-to-Ambient ³ | $R_{\theta JA}$ | 53 | $^\circ C/W$ |
| Thermal Resistance from Junction-to-Case | $R_{\theta JC}$ | 2.9 | $^\circ C/W$ |

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit | |
|--|----------------------|--|-----------------------|------|------|------|----|
| Static Characteristics | | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0V, I _D = 250μA | 65 | - | - | V | |
| Gate-body Leakage Current | I _{GSS} | V _{DS} = 0V, V _{GS} = ±20V | - | - | ±100 | nA | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 65V, V _{GS} = 0V | T _J =25°C | - | - | 1 | μA |
| | | | T _J =100°C | - | - | 100 | |
| Gate-Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250μA | 2.5 | 2.9 | 3.5 | V | |
| Drain-Source On-Resistance ⁴ | R _{DS(on)} | V _{GS} = 10V, I _D = 20A | - | 4.5 | 5.5 | mΩ | |
| Forward Transconductance ⁴ | g _{fs} | V _{DS} = 10V, I _D = 20A | - | 89 | - | S | |
| Dynamic Characteristics⁵ | | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 30V, V _{GS} = 0V, f = 1MHz | - | 1735 | - | pF | |
| Output Capacitance | C _{oss} | | - | 670 | - | | |
| Reverse Transfer Capacitance | C _{rss} | | - | 32 | - | | |
| Gate Resistance | R _g | f = 1MHz | - | 1.8 | - | Ω | |
| Switching Characteristics⁵ | | | | | | | |
| Total Gate Charge | Q _g | V _{GS} = 10V, V _{DS} = 30V, I _D = 20A | - | 28.5 | - | nC | |
| Gate-Source Charge | Q _{gs} | | - | 7.8 | - | | |
| Gate-Drain Charge | Q _{gd} | | - | 8.4 | - | | |
| Turn-On Delay Time | t _{d(on)} | V _{GS} = 10V, V _{DD} = 30V, R _G = 3Ω, I _D = 20A | - | 11.2 | - | ns | |
| Rise Time | t _r | | - | 8.2 | - | | |
| Turn-Off Delay Time | t _{d(off)} | | - | 19.6 | - | | |
| Fall Time | t _f | | - | 6.2 | - | | |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 20A, di/dt = 100A/μs | - | 50 | - | ns | |
| Body Diode Reverse Recovery Charge | Q _{rr} | | - | 20 | - | nC | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Diode Forward Voltage ⁴ | V _{SD} | I _S = 20A, V _{GS} = 0V | - | - | 1.2 | V | |
| Continuous Source Current | I _S | T _C = 25°C | - | - | 68 | A | |

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD} = 25V, V_{GS} = 10V, L = 0.4mH, I_{AS} = 26A.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

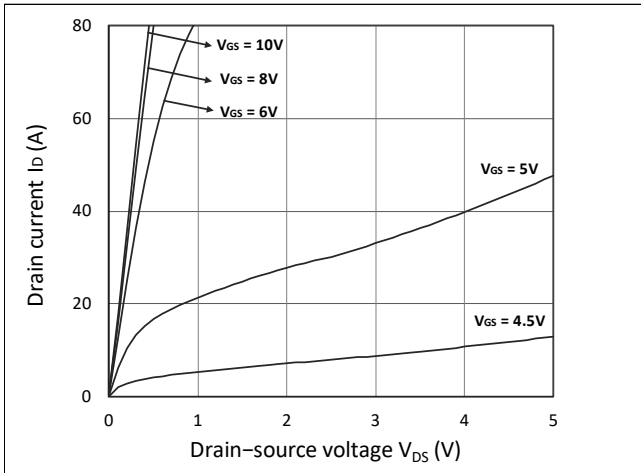


Figure 1. Output Characteristics

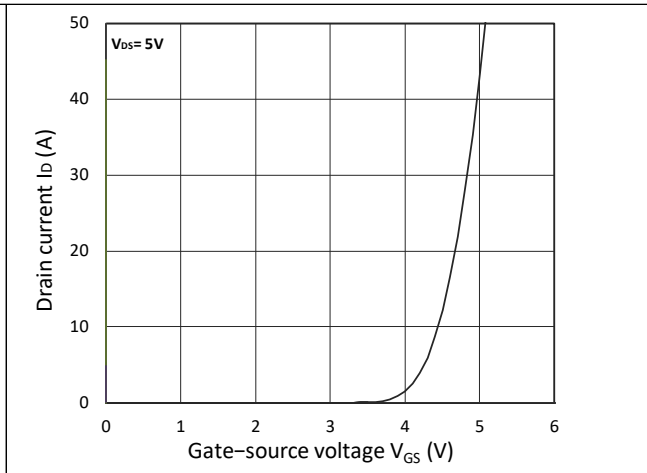


Figure 2. Transfer Characteristics

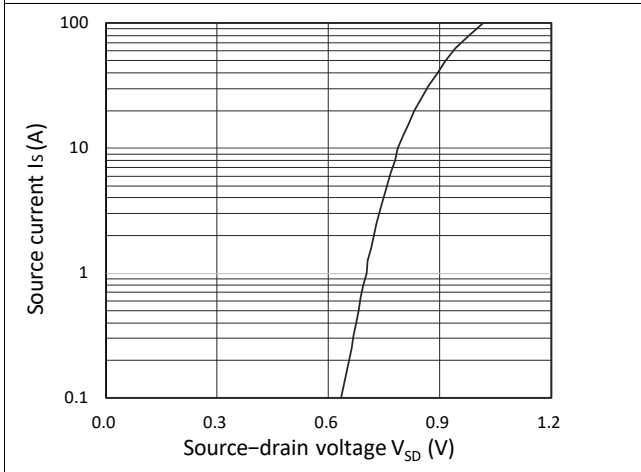


Figure 3. Forward Characteristics of Reverse

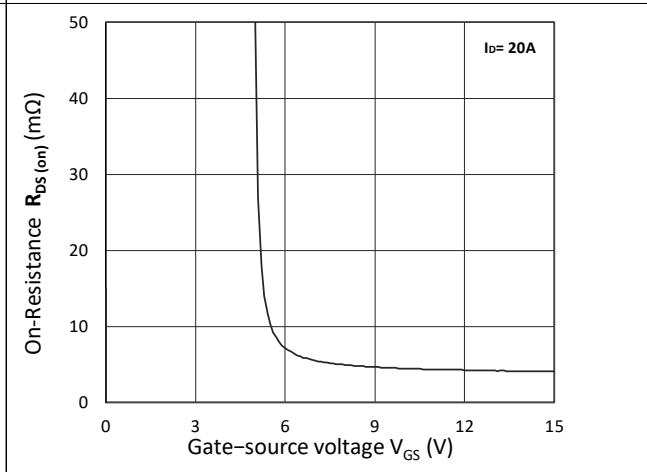


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

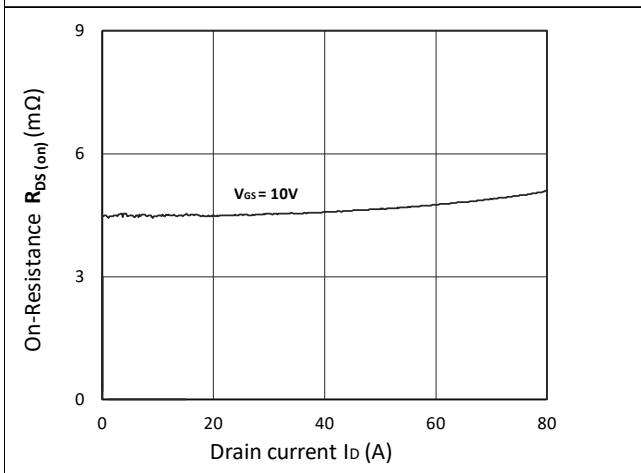


Figure 5. $R_{DS(ON)}$ vs. I_D

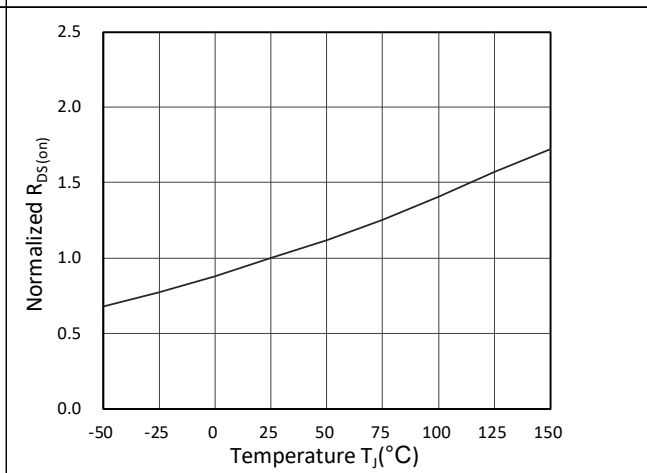


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

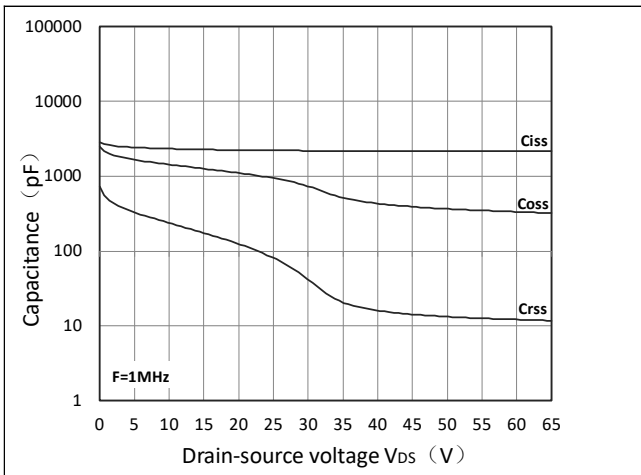


Figure 7. Capacitance Characteristics

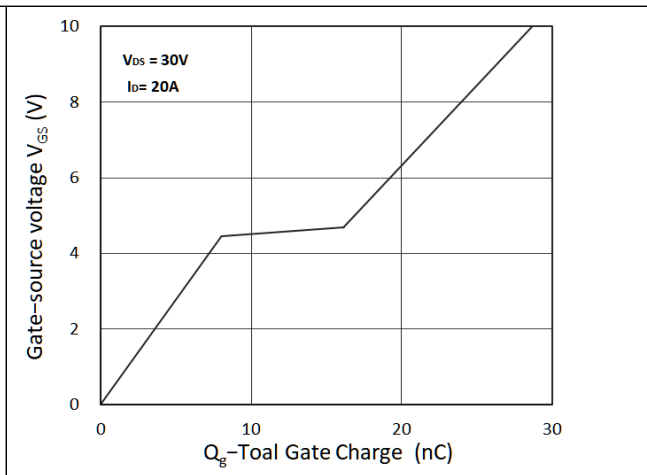


Figure 8. Gate Charge Characteristics

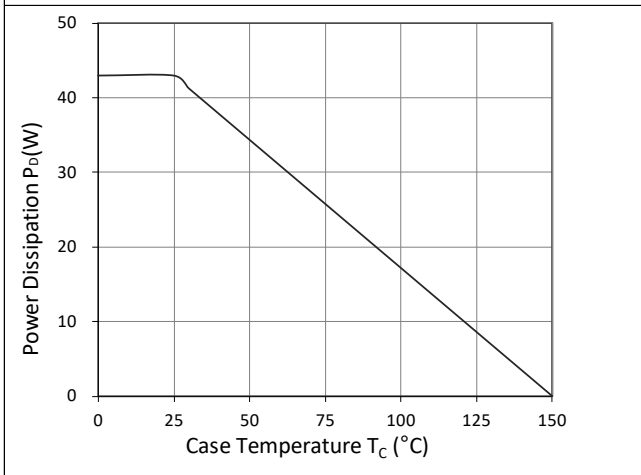


Figure 9. Power Dissipation

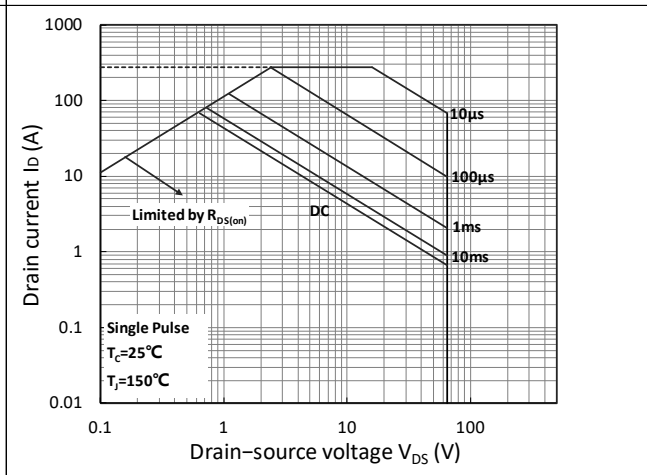


Figure 10. Safe Operating Area

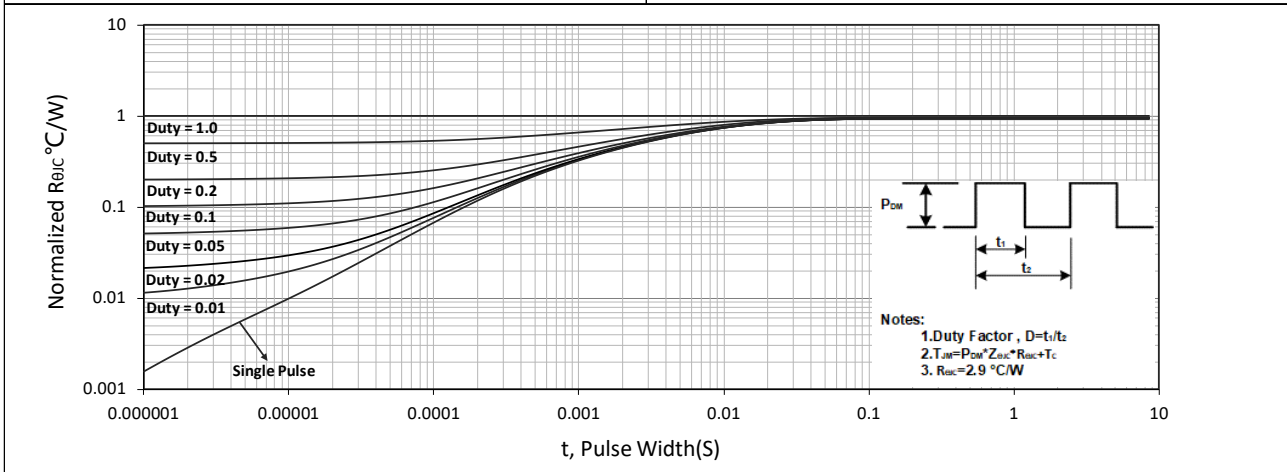


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

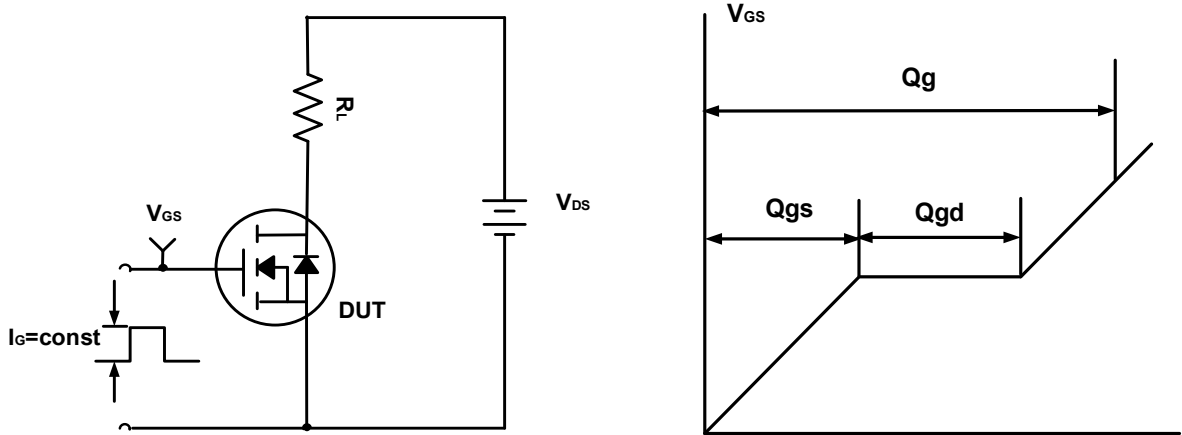


Figure A. Gate Charge Test Circuit & Waveforms

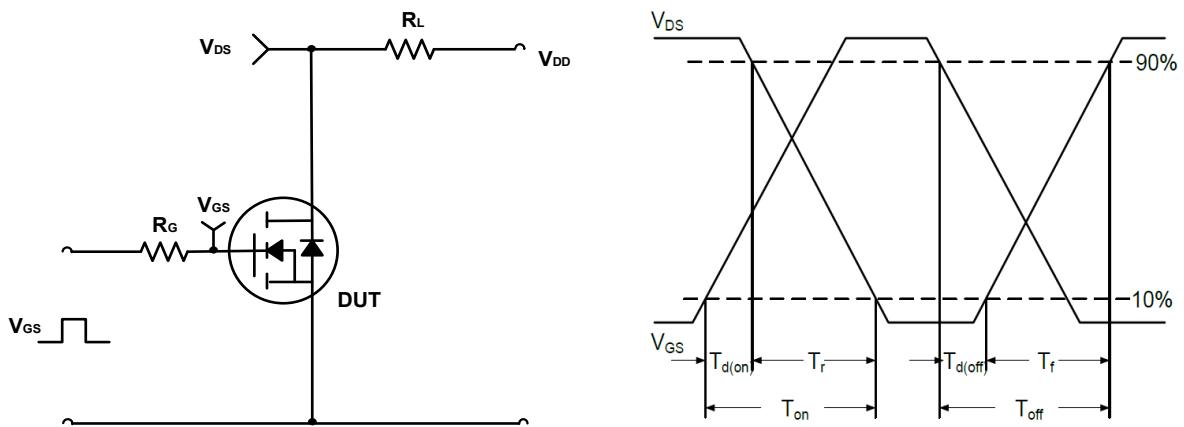


Figure B. Switching Test Circuit & Waveforms

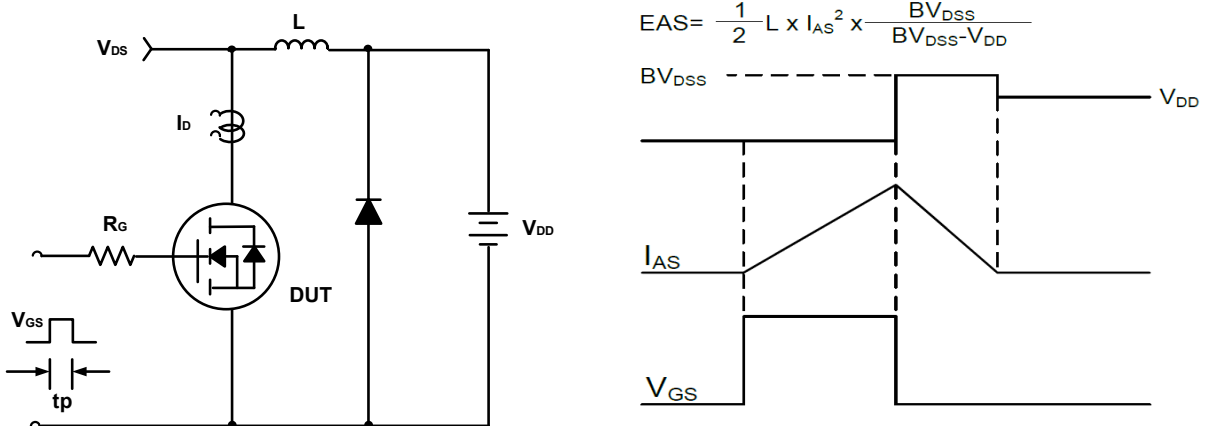
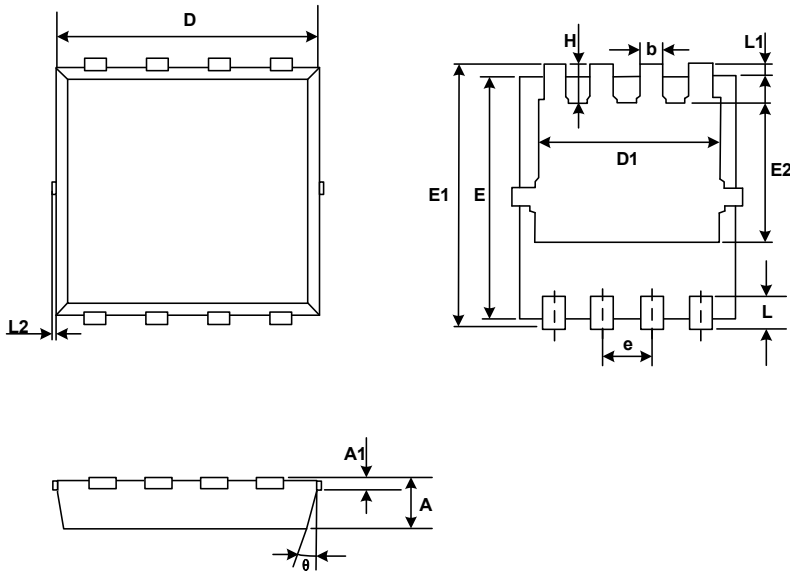


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Mechanical Dimensions for PDFN3030-8L



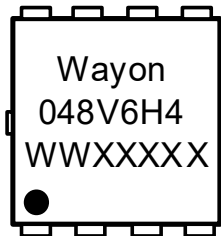
COMMON DIMENSIONS

| SYMBOL | MM | |
|--------|---------|------|
| | MIN | MAX |
| A | 0.65 | 0.90 |
| A1 | 0.10 | 0.25 |
| D | 2.90 | 3.25 |
| D1 | 2.25 | 2.69 |
| E | 2.90 | 3.20 |
| E1 | 3.00 | 3.60 |
| E2 | 1.35 | 2.20 |
| b | 0.20 | 0.40 |
| e | 0.65BSC | |
| L | 0.15 | 0.50 |
| L1 | 0.13BSC | |
| L2 | 0.00 | 0.20 |
| H | 0.15 | 0.65 |
| θ | 0° | 14° |

Ordering Information

| Part | Package | Marking | Packing method |
|--------------|-------------|---------|----------------|
| WMQ048NV6HG4 | PDFN3030-8L | 048V6H4 | Tape and Reel |

Marking Information



048V6H4= Device code

WWXXXXX= Date code


Contact Information.

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